

Fig. 7. Digital delay and correction logic schematic. Only one circuit is shown.

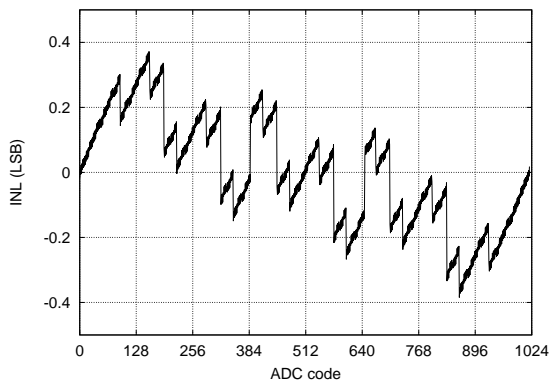


Fig. 8. Typical INL curve of the ADC.

C. Digital circuitry

Digital circuitry includes delay equalizing registers and digital correction for each ADC pipeline. Fig. 7 shows the schematic of these circuits. All registers are dynamic, of C²MOS type, allowing a very compact layout and low-power operation. The digital correction algorithm is merely the addition of all redundant bits together. These circuits are implemented as 9-bit, serial-carry, adders. No fast-carry logic is needed for this clock frequency.

Digital circuitry runs on a separate power bus. An additional 3.3 V power line is provided for pin drivers. The power consumption of the digital logic, excluding pin drivers, was estimated at 1.75 mW from extracted circuit simulation.

IV. SIMULATION RESULTS.

Two different types of simulation were carried out in order to test the design robustness. First, a behavioral model simulator was written in C language. This simulator includes the effects of capacitor mismatching, finite opamp gain and comparator offset. The digital correction algorithm was also included in the simulation. A Monte-Carlo simulation was carried out by simulating a large number (10000) of different ADCs with Gaussian random varia-

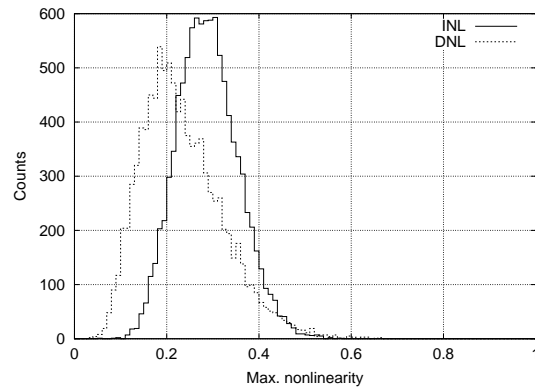


Fig. 9. Monte-Carlo results for the ADC's maximum nonlinearity. Solid line: INL. Dotted line: DNL.

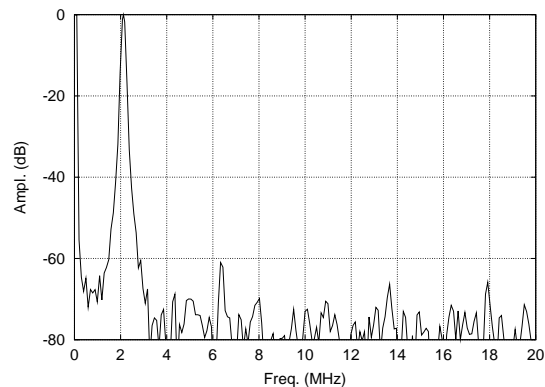


Fig. 10. Spectrum of a digitally converted sinusoid obtained from a transistor-level simulation.

tions in their capacitor values and comparator offsets. In this simulation the key component values were:

| | |
|----------------------|------------------|
| C_s , First stage | 0.8 pF |
| C_s , Second stage | 0.2 pF |
| C_s , Stages 3-8 | 0.1 pF |
| opamp's DC gain | 70 dB |
| comparator offset | $\sigma = 10$ mV |

The nonlinearity of each ADC was analyzed by finding the threshold voltage of each ADC code. Fig 8 shows a typical integral nonlinearity graph (INL) for an ADC with random variations in its component values. The histograms of Fig. 9 were built by finding the maximum absolute nonlinearity of each ADC. This figure shows that, using the proposed design parameters, the 99% of ADCs have a maximum INL and DNL below 0.5 LSB.

Other simulations were carried out after the completion of the test chip layout by using Spectre and an extracted netlist from the layout. This netlist included about 45000 devices, most of them parasitic capacitances, and, therefore, these simulations were very time consuming. The correct behavior of the ADC, at the transistor level, was proven in this way. Fig. 10 shows the output spectrum after A-to-D conversion for a full-scale, single tone input. Due to the long time required, only 400 ADC samples were recorded, but they are enough to show that the harmonic distortion is less than -60 dB. In this simulation the capacitor mismatching was not included. The observed distor-

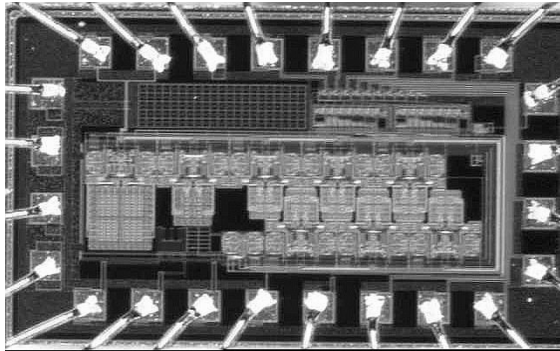


Fig. 11. Chip photograph.

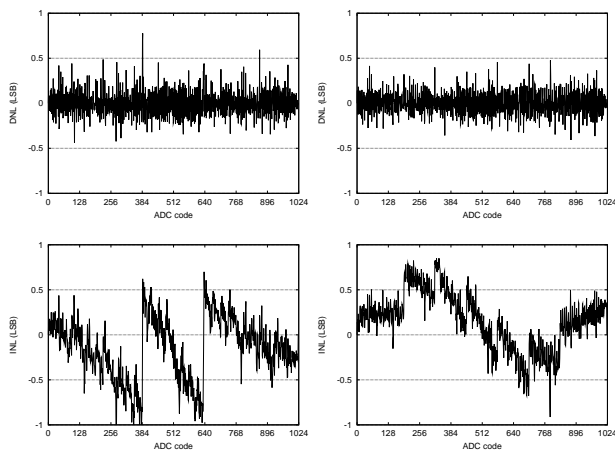


Fig. 12. Differential nonlinearity (DNL) and integral nonlinearity (INL) for the two pipelines of the ADC.

tion is due to finite opamp gain, incomplete opamp settling due to finite bandwidth, and other dynamic phenomena like charge injection from switches. The extracted circuit simulation also gave us a confident estimation of the power consumption of the chip.

V. EXPERIMENTAL RESULTS

The proposed ADC was fabricated in the Agere's 0.25- μm CMOS technology. The chip photograph is shown in Fig. 11. The unpackaged die was bonded to a PCB board that included, among other components, decoupling capacitors for power supplies and buffers for digital outputs. Several tests were carried-out to measure the ADC's performance.

First, the linearity of both ADC's pipelines were measured following the code-density approach [11]. The results are displayed on Fig 12. The measured nonlinearities have an average value about 0.5 LSB, but the peak values are higher. These curves show that the ADC is monotonic and there are no missing codes. The mismatch between the INL of the two pipelines can generate tones at frequencies $f_n = f_s/2 - n \cdot f_{in}$. The offset and gain differences are responsible for tones at $f_s/2$ and $f_s/2 - f_{in}$ respectively [8] while higher order mismatches generate spur tones farther apart from the Nyquist frequency. Because the INL error is lower than 1 LSB these spurs are always lower than -60

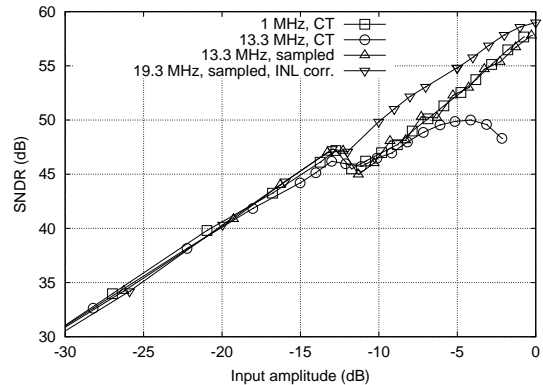


Fig. 13. Measured signal to noise and distortion ratios (SNDR) for several input frequencies and conditions.

TABLE I
ADC PERFORMANCE

| | |
|---------------------|--|
| Resolution | 10 bits |
| Sampling Rate | 40 MHz |
| Power consumption | ADC: 11.7 mW Pin drivers: 1.3 mW ($C_L \approx 4.5$ pF) |
| Technology | 2.5 V 0.25- μm CMOS (MOM cap.) |
| Chip Area (w. pads) | 1.5 \times 0.88 mm ² |
| Nonlinearity (max) | DNL: 0.77 LSB INL: 1.15 LSB |
| SNR (max) | 61.3 dB @ 10.6 MHz |
| SNDR (max) | 57.6 dB @ 1 MHz 57.8 dB @ 19.3 MHz [†] |
| ENOB (max) | 9.3 bits @ 1 MHz 9.3 bits @ 19.3 MHz [†] |

[†] Sampled input, without static INL correction.

dB. The INL tables of Fig 12 can be used to correct the linearity of the converter in the digital domain by subtracting the measured linearity error to the output. This technique can achieve an improved linearity and matching between pipelines, but requires calibration.

The dynamic performance of the ADC was measured by applying a single tone to the inputs and analyzing the recorded code stream in the frequency domain. Fig 13 shows the measured signal to noise and distortion ratio (SNDR) for several input frequencies and conditions. The SNDR curves show an abrupt drop for input amplitudes around -12 dB. This is due to the big INL transitions of one pipeline for input amplitudes of 1/4 of full scale. The SNDR also drops gradually for high frequency inputs. This problem was found to be due to the nonlinear resistance of the switches in the first pipeline stage, and it is only present if the input is a continuous-time (CT) signal. To prove this point a sampled sinusoid was applied to the input and the resulting SNDR curve showed no performance drop. Finally, after applying the INL correction mentioned before, the obtained SNDR curve shows a very little performance loss, even for input frequencies close to Nyquist, if the input signal is sampled.

The measured ADC performance is summarized on Table I. It is worth mentioning the low power achieved.

VI. CONCLUSIONS

In this work a dual-pipeline, time-interleaved, CMOS ADC is designed in a 0.25 μm CMOS technology with metal-oxide-metal capacitor option. This ADC has a sampling rate of 40 MHz, and it provides 10 bits of resolution. The power consumption is only 12 mW. This low power is achieved mainly by sharing operational amplifiers between pipelines and by the use of digital correction for comparator offsets. Our simulations shows that good linearity and high yield can be achieved without applying any calibration technique.

The experimental results were close to simulations when the input signal is sampled. In order to improve the linearity for high-frequency, continuous-time inputs a SHA must be inserted before the ADC. Our power estimation for such SHA is about 4 mW. Alternatively, the switches of the first pipeline stages can be replaced with highly linear, bootstrapped switches. The matching between pipelines and the linearity of the ADC can be improved by using INL correction. This technique can raise the resolution of the measured converter by about 0.5 effective bits. Because the INL of the converter have to be measured before the correction can be implemented, the increased circuit complexity would be only justified for critical applications.

VII. ACKNOWLEDGMENT

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